Jin-Seong Park

List of Publications by Year
in descending order

265 papers	11,700 citations	36303 51 h-index	34986 98 g-index
267 all docs	267 docs citations	267 times ranked	8278 citing authors

#	Article	IF	Citations
1	Review of recent developments in amorphous oxide semiconductor thin-film transistor devices. Thin Solid Films, 2012, 520, 1679-1693.	1.8	905
2	Electronic transport properties of amorphous indium-gallium-zinc oxide semiconductor upon exposure to water. Applied Physics Letters, 2008, 92, .	3.3	461
3	High mobility bottom gate InGaZnO thin film transistors with SiOx etch stopper. Applied Physics Letters, 2007, 90, 212114.	3.3	427
4	Flexible full color organic light-emitting diode display on polyimide plastic substrate driven by amorphous indium gallium zinc oxide thin-film transistors. Applied Physics Letters, 2009, 95, .	3.3	414
5	Thin film encapsulation for flexible AM-OLED: a review. Semiconductor Science and Technology, 2011, 26, 034001.	2.0	388
6	High performance thin film transistors with cosputtered amorphous indium gallium zinc oxide channel. Applied Physics Letters, 2007, 91, .	3.3	364
7	Improvements in the device characteristics of amorphous indium gallium zinc oxide thin-film transistors by Ar plasma treatment. Applied Physics Letters, 2007, 90, 262106.	3.3	325
8	Synthesis and Characterization of Volatile, Thermally Stable, Reactive Transition Metal Amidinates. Inorganic Chemistry, 2003, 42, 7951-7958.	4.0	267
9	Novel ZrInZnO Thinâ€ffilm Transistor with Excellent Stability. Advanced Materials, 2009, 21, 329-333.	21.0	249
10	Amorphous hafnium-indium-zinc oxide semiconductor thin film transistors. Applied Physics Letters, 2009, 95, .	3.3	217
11	Origin of Subthreshold Swing Improvement in Amorphous Indium Gallium Zinc Oxide Transistors. Electrochemical and Solid-State Letters, 2008, 11, H157.	2.2	208
12	Comparison of the effects of Ar and H2 plasmas on the performance of homojunctioned amorphous indium gallium zinc oxide thin film transistors. Applied Physics Letters, 2008, 93, .	3.3	191
13	Amorphous IGZO TFT with High Mobility of â^¼70 cm²/(V s) via Vertical Dimension Control Using PEALD. ACS Applied Materials & Interfaces, 2019, 11, 40300-40309.	8.0	188
14	3.1: Distinguished Paper: 12.1â€Inch WXGA AMOLED Display Driven by Indiumâ€Galliumâ€Zinc Oxide TFTs Array. Digest of Technical Papers SID International Symposium, 2008, 39, 1-4.	0.3	180
15	High performance thin film transistor with low temperature atomic layer deposition nitrogen-doped ZnO. Applied Physics Letters, 2007, 91, .	3.3	166
16	Control of threshold voltage in ZnO-based oxide thin film transistors. Applied Physics Letters, 2008, 93, .	3.3	162
17	The influence of the gate dielectrics on threshold voltage instability in amorphous indium-gallium-zinc oxide thin film transistors. Applied Physics Letters, 2009, 95, .	3.3	151
18	Atomic Layer Deposition of Y2O3Thin Films from Yttrium Tris(N,Nâ€˜-diisopropylacetamidinate) and Water. Chemistry of Materials, 2005, 17, 4808-4814.	6.7	134

#	Article	IF	Citations
19	Flexible and High-Performance Amorphous Indium Zinc Oxide Thin-Film Transistor Using Low-Temperature Atomic Layer Deposition. ACS Applied Materials & Interfaces, 2016, 8, 33821-33828.	8.0	124
20	Efficient Planar Perovskite Solar Cells Using Passivated Tin Oxide as an Electron Transport Layer. Advanced Science, 2018, 5, 1800130.	11.2	120
21	Overview of electroceramic materials for oxide semiconductor thin film transistors. Journal of Electroceramics, 2014, 32, 117-140.	2.0	117
22	Plasma-Enhanced Atomic Layer Deposition of Ta-N Thin Films. Journal of the Electrochemical Society, 2002, 149, C28.	2.9	113
23	The impact of gate dielectric materials on the light-induced bias instability in Hfâ€“Inâ€“Znâ€“O thin film transistor. Applied Physics Letters, 2010, 97, 183503.	3.3	106
24	Enhanced charge collection with passivation of the tin oxide layer in planar perovskite solar cells. Journal of Materials Chemistry A, 2017, 5, 12729-12734.	10.3	103
25	Atomic Layer Deposition of an Indium Gallium Oxide Thin Film for Thin-Film Transistor Applications. ACS Applied Materials & Interfaces, 2017, 9, 23934-23940.	8.0	97
26	Review of recent advances in flexible oxide semiconductor thin-film transistors. Journal of Information Display, 2017, 18, 159-172.	4.0	97
27	A review on the recent developments of solution processes for oxide thin film transistors. Semiconductor Science and Technology, 2015, 30, 064001.	2.0	83
28	Review Article: Atomic layer deposition for oxide semiconductor thin film transistors: Advances in research and development. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2018, 36, .	2.1	82
29	Highly Transparent, Visible-Light Photodetector Based on Oxide Semiconductors and Quantum Dots. ACS Applied Materials & Interfaces, 2015, 7, 19666-19671.	8.0	80
30	Low temperature Ga2O3 atomic layer deposition using gallium tri-isopropoxide and water. Thin Solid Films, 2013, 546, 31-34.	1.8	77
31	Highly conductive SnO2 thin films deposited by atomic layer deposition using tetrakis-dimethyl-amine-tin precursor and ozone reactant. Surface and Coatings Technology, 2014, 259, 238-243.	4.8	71
32	Impact of high-kâ€ˆTiOx dielectric on device performance of indium-gallium-zinc oxide transistors. Applied Physics Letters, 2009, 94, .	3.3	70
33	Plasma-Enhanced Atomic Layer Deposition of Tantalum Nitrides Using Hydrogen Radicals as a Reducing Agent. Electrochemical and Solid-State Letters, 2001, 4, C17.	2.2	69
34	The effects of buffer layers on the performance and stability of flexible InGaZnO thin film transistors on polyimide substrates. Applied Physics Letters, 2014, 104, .	3.3	69
35	Control of valley degeneracy in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>Mo</mml:mi><mml:msub><mml:mi mathvariant="normal">S</mml:mi><mml:mn>2</mml:mn></mml:msub></mml:mrow></mml:math>by layer thickness and electric field and its effect on thermoelectric properties. Physical Review B, 2016, 93, .	3.2	68
36	Review of Organic/Inorganic Thin Film Encapsulation by Atomic Layer Deposition for a Flexible OLED Display. Jom, 2019, 71, 197-211.	1.9	68

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37	High tunability (Ba,Sr)TiO3 thin films grown on atomic layer deposited TiO2 and Ta2O5 buffer layers. Applied Physics Letters, 2004, 85, 4705-4707.	3.3	65
38	12.1â€in. WXGA AMOLED display driven by InGaZnO thinâ€film transistors. Journal of the Society for Information Display, 2009, 17, 95-100.	2.1	65
39	Studies on optical, structural and electrical properties of atomic layer deposited Al-doped ZnO thin films with various Al concentrations and deposition temperatures. Journal Physics D: Applied Physics, 2011, 44, 445305.	2.8	64
40	Double gate GaInZnO thin film transistors. Applied Physics Letters, 2008, 93, .	3.3	62
41	Meyerâ€“Neldel Rule and Extraction of Density of States in Amorphous Indiumâ€“Galliumâ€“Zinc-Oxide Thin-Film Transistor by Considering Surface Band Bending. Japanese Journal of Applied Physics, 2010, 49, 03CB02.	1.5	62
42	A Study on the Electrical Properties of Atomic Layer Deposition Grown InO_x on Flexible Substrates with Respect to N₂O Plasma Treatment and the Associated Thin-Film Transistor Behavior under Repetitive Mechanical Stress. ACS Applied Materials & Interfaces, 2016, 8, 31136-31143.	8.0	62
43	Low-Temperature Growth of Indium Oxide Thin Film by Plasma-Enhanced Atomic Layer Deposition Using Liquid Dimethyl(N-ethoxy-2,2-dimethylpropanamido)indium for High-Mobility Thin Film Transistor Application. ACS Applied Materials & Interfaces, 2016, 8, 26924-26931.	8.0	59
44	Highly Conducting, Transparent, and Flexible Indium Oxide Thin Film Prepared by Atomic Layer Deposition Using a New Liquid Precursor Et₂InN(SiMe₃)₂. ACS Applied Materials & Interfaces, 2014, 6, 17481-17488.	8.0	58
45	Rational design of protective In2O3 layer-coated carbon nanopaper membrane: Toward stable cathode for long-cycle Li-O2 batteries. Nano Energy, 2018, 46, 193-202.	16.0	58
46	Tantalum(V) Nitride Inverse Opals as Photonic Structures for Visible Wavelengths. Journal of Physical Chemistry B, 2005, 109, 3764-3771.	2.6	57
47	Effects of porosity and particle size on the gas sensing properties of SnO2 films. Applied Surface Science, 2019, 481, 133-137.	6.1	57
48	Atomic layer deposited p-type copper oxide thin films and the associated thin film transistor properties. Ceramics International, 2016, 42, 5517-5522.	4.8	55
49	A study of thin film encapsulation on polymer substrate using low temperature hybrid ZnO/Al2O3 layers atomic layer deposition. Current Applied Physics, 2012, 12, S19-S23.	2.4	54
50	A Novel Amorphous InGaZnO Thin Film Transistor Structure without Source/Drain Layer Deposition. Japanese Journal of Applied Physics, 2009, 48, 03B019.	1.5	52
51	Atomic Layer Deposition ZnO:N Thin Film Transistor: The Effects of N Concentration on the Device Properties. Journal of the Electrochemical Society, 2010, 157, H214.	2.9	52
52	Study of Nitrogen High-Pressure Annealing on InGaZnO Thin-Film Transistors. ACS Applied Materials & Interfaces, 2014, 6, 13496-13501.	8.0	52
53	Indium oxide thin film prepared by low temperature atomic layer deposition using liquid precursors and ozone oxidant. Journal of Alloys and Compounds, 2015, 649, 216-221.	5.5	51
54	Bulk-Limited Current Conduction in Amorphous InGaZnO Thin Films. Electrochemical and Solid-State Letters, 2008, 11, H51.	2.2	50

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55	Performance and Stability Enhancement of Inâ€“Snâ€“Znâ€“O TFTs Using SiO₂ Gate Dielectrics Grown by Low Temperature Atomic Layer Deposition. ACS Applied Materials & Interfaces, 2017, 9, 42928-42934.	8.0	50
56	Design of InZnSnO Semiconductor Alloys Synthesized by Supercycle Atomic Layer Deposition and Their Rollable Applications. ACS Applied Materials & Interfaces, 2019, 11, 12683-12692.	8.0	49
57	Review of recent progresses on flexible oxide semiconductor thin film transistors based on atomic layer deposition processes. Journal of Semiconductors, 2018, 39, 011008.	3.7	48
58	The conducting tin oxide thin films deposited via atomic layer deposition using Tetrakis-dimethylamino tin and peroxide for transparent flexible electronics. Applied Surface Science, 2014, 313, 585-590.	6.1	47
59	Atomic layer deposition of highly conductive indium oxide using a liquid precursor and water oxidant. Ceramics International, 2015, 41, 10782-10787.	4.8	47
60	Low temperature atomic layer deposition of SiO2 thin films using di-isopropylaminosilane and ozone. Ceramics International, 2017, 43, 2095-2099.	4.8	47
61	Gas diffusion barrier characteristics of Al2O3/alucone films formed using trimethylaluminum, water and ethylene glycol for organic light emitting diode encapsulation. Thin Solid Films, 2013, 546, 153-156.	1.8	46
62	Effect of Al concentration on the electrical characteristics of solution-processed Al doped ZnSnO thin film transistors. Ceramics International, 2014, 40, 8769-8774.	4.8	46
63	Highly efficient and stable flexible perovskite solar cells enabled by using plasma-polymerized-fluorocarbon antireflection layer. Nano Energy, 2021, 82, 105737.	16.0	46
64	MOSFET-Like Behavior of a-InGaZnO Thin-Film Transistors With Plasma-Exposed Sourceâ€“Drain Bulk Region. Journal of Display Technology, 2009, 5, 495-500.	1.2	45
65	Highly Stable ZnON Thin-Film Transistors With High Field-Effect Mobility Exceeding 50 <inline-formula> <tex-math notation="LaTeX">$mathrm{cm}^{2}$ </tex-math></inline-formula>/Vs. IEEE Electron Device Letters, 2015, 36, 38-40.	3.9	45
66	Low Voltage Operating Field Effect Transistors with Composite In₂O₃â€“ZnOâ€“ZnGa₂O₄ Nanofiber Network as Active Channel Layer. ACS Nano, 2014, 8, 2318-2327.	14.6	44
67	The effect of thermal annealing sequence on amorphous InGaZnO thin film transistor with a plasma-treated sourceâ€“drain structure. Thin Solid Films, 2009, 517, 6349-6352.	1.8	43
68	The impact of SiNx gate insulators on amorphous indium-gallium-zinc oxide thin film transistors under bias-temperature-illumination stress. Applied Physics Letters, 2010, 96, 193506.	3.3	43
69	Stability Improvement of In-Sn-Ga-O Thin-Film Transistors at Low Annealing Temperatures. IEEE Electron Device Letters, 2015, 36, 1160-1162.	3.9	43
70	Facile Route to the Controlled Synthesis of Tetragonal and Orthorhombic SnO₂ Films by Mist Chemical Vapor Deposition. ACS Applied Materials & Interfaces, 2015, 7, 12074-12079.	8.0	43
71	Performance modulation of transparent ALD indium oxide films on flexible substrates: transition between metal-like conductor and high performance semiconductor states. Journal of Materials Chemistry C, 2016, 4, 7571-7576.	5.5	43
72	Ambient atmosphere-processable, printable Cu electrodes for flexible device applications: structural welding on a millisecond timescale of surface oxide-free Cu nanoparticles. Nanoscale, 2015, 7, 3997-4004.	5.6	42

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73	Phase-controlled SnO2 and SnO growth by atomic layer deposition using Bis(N-ethoxy-2,2-dimethyl) Tj ETQq1 1 0.784314 rgBT /Over	4.8	42
74	Enhanced mobility of Li-doped ZnO thin film transistors fabricated by mist chemical vapor deposition. Applied Surface Science, 2014, 301, 358-362.	6.1	41
75	Effect of Alumina Buffers on the Stability of Top-Gate Amorphous InGaZnO Thin-Film Transistors on Flexible Substrates. IEEE Electron Device Letters, 2015, 36, 917-919.	3.9	41
76	Controlled growth and properties of p-type cuprous oxide films by plasma-enhanced atomic layer deposition at low temperature. Applied Surface Science, 2013, 285, 373-379.	6.1	40
77	Device performance and bias instability of Ta doped InZnO thin film transistor as a function of process pressure. Applied Physics Letters, 2013, 102, .	3.3	40
78	Control of phonon transport by the formation of the Al₂O₃ interlayer in Al₂O₃â€“ZnO superlattice thin films and their in-plane thermoelectric energy generator performance. Nanoscale, 2017, 9, 7027-7036.	5.6	40
79	Kinetic modeling of film growth rates of TiN films in atomic layer deposition. Journal of Applied Physics, 2000, 87, 4632-4634.	2.5	39
80	The influence of oxygen partial pressure on the performance and stability of Ge-doped InGaO thin film transistors. Ceramics International, 2014, 40, 3215-3220.	4.8	39
81	Facile fabrication of high-performance InGaZnO thin film transistor using hydrogen ion irradiation at room temperature. Applied Physics Letters, 2014, 105, .	3.3	38
82	A study on the electron transport properties of ZnON semiconductors with respect to the relative anion content. Scientific Reports, 2016, 6, 24787.	3.3	38
83	Undoped ZnO electrodes for low-cost indoor organic photovoltaics. Journal of Materials Chemistry A, 2018, 6, 23464-23472.	10.3	38
84	High Reliable and Manufacturable Gallium Indium Zinc Oxide Thin-Film Transistors Using the Double Layers as an Active Layer. Journal of the Electrochemical Society, 2009, 156, H184.	2.9	36
85	A Study on the Growth Behavior and Stability of Molecular Layer Deposited Alucone Films Using Diethylene Glycol and Trimethyl Aluminum Precursors, and the Enhancement of Diffusion Barrier Properties by Atomic Layer Deposited Al₂O₃ Capping. ACS Applied Materials & Interfaces, 2016, 8, 12263-12271.	8.0	36
86	Undoped tin dioxide transparent electrodes for efficient and cost-effective indoor organic photovoltaics (SnO2 electrode for indoor organic photovoltaics). NPG Asia Materials, 2021, 13, .	7.9	36
87	Thermal Evolution of Band Edge States in ZnO Film as a Function of Annealing Ambient Atmosphere. Electrochemical and Solid-State Letters, 2012, 15, H133.	2.2	35
88	The effect of the annealing temperature on the transition from conductor to semiconductor behavior in zinc tin oxide deposited atomic layer deposition. Applied Physics Letters, 2014, 105, .	3.3	35
89	Electronic structure of conducting Al-doped ZnO films as a function of Al doping concentration. Ceramics International, 2015, 41, 1641-1645.	4.8	35
90	Super-hydrophobic and antimicrobial properties of Ag-PPFC nanocomposite thin films fabricated using a ternary carbon nanotube-Ag-PTFE composite sputtering target. Surface and Coatings Technology, 2019, 370, 18-23.	4.8	35

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91	A role of oxygen vacancy on annealed ZnO film in the hydrogen atmosphere. Current Applied Physics, 2012, 12, S164-S167.	2.4	34
92	Effect of hydrogen on the device performance and stability characteristics of amorphous InGaZnO thin-film transistors with a SiO2/SiNx/SiO2 buffer. Applied Physics Letters, 2017, 111, .	3.3	34
93	Metastable Rhombohedral Phase Transition of Semiconducting Indium Oxide Controlled by Thermal Atomic Layer Deposition. Chemistry of Materials, 2020, 32, 7397-7403.	6.7	33
94	The characteristics of organic light emitting diodes with Al doped zinc oxide grown by atomic layer deposition as a transparent conductive anode. Synthetic Metals, 2011, 161, 823-827.	3.9	32
95	The influence of visible light on the gate bias instability of Inâ€“Gaâ€“Znâ€“O thin film transistors. Solid-State Electronics, 2011, 62, 77-81.	1.4	32
96	Enhancing the thermoelectric properties of super-lattice Al2O3/ZnO atomic film via interface confinement. Ceramics International, 2016, 42, 14411-14415.	4.8	32
97	Hydrogen Impacts of PEALD InGaZnO TFTs Using SiO_x Gate Insulators Deposited by PECVD and PEALD. IEEE Transactions on Electron Devices, 2020, 67, 4250-4255.	3.0	32
98	Effects of Ga:N Addition on the Electrical Performance of Zinc Tin Oxide Thin Film Transistor by Solution-Processing. ACS Applied Materials & Interfaces, 2014, 6, 9228-9235.	8.0	30
99	Effect of mechanical stress on the stability of flexible InGaZnO thin-film transistors. Journal of Information Display, 2017, 18, 87-91.	4.0	30
100	Comparative studies on the physical and electronic properties of reactively sputtered ZnO and ZnON semiconductors. Ceramics International, 2015, 41, 13281-13284.	4.8	29
101	Selective SnO_x Atomic Layer Deposition Driven by Oxygen Reactants. ACS Applied Materials & Interfaces, 2018, 10, 33335-33342.	8.0	28
102	Highly Dense and Stable p-Type Thin-Film Transistor Based on Atomic Layer Deposition SnO Fabricated by Two-Step Crystallization. ACS Applied Materials & Interfaces, 2021, 13, 30818-30825.	8.0	28
103	Studies of thermoelectric transport properties of atomic layer deposited gallium-doped ZnO. Ceramics International, 2017, 43, 7784-7788.	4.8	27
104	Low temperature SiOx thin film deposited by plasma enhanced atomic layer deposition for thin film encapsulation applications. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2017, 35, .	2.1	26
105	Low temperature atomic layer deposited Al-doped ZnO thin films and associated semiconducting properties. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2012, 30, 031210.	1.2	25
106	Boosting Responsivity of Organicâ€“Metal Oxynitride Hybrid Heterointerface Phototransistor. ACS Applied Materials & Interfaces, 2016, 8, 14665-14670.	8.0	25
107	Effects of Repetitive Mechanical Stress on Flexible Oxide Thin-Film Transistors and Stress Reduction via Additional Organic Layer. IEEE Electron Device Letters, 2018, 39, 971-974.	3.9	24
108	Growth characteristics and film properties of gallium doped zinc oxide prepared by atomic layer deposition. Journal of Electroceramics, 2013, 31, 338-344.	2.0	23

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109	Improvement of Negative Bias Temperature Illumination Stability of Amorphous IGZO Thin-Film Transistors by Water Vapor-Assisted High-Pressure Oxygen Annealing. ECS Journal of Solid State Science and Technology, 2014, 3, Q95-Q98.	1.8	23
110	High-Performance Zinc Tin Oxide Semiconductor Grown by Atmospheric-Pressure Mist-CVD and the Associated Thin-Film Transistor Properties. ACS Applied Materials & Interfaces, 2017, 9, 20656-20663.	8.0	23
111	Selective Nonenzymatic Amperometric Detection of Lactic Acid in Human Sweat Utilizing a Multi-Walled Carbon Nanotube (MWCNT)-Polypyrrole Core-Shell Nanowire. Biosensors, 2020, 10, 111.	4.7	23
112	Investigation of Light-Induced Bias Instability in Hf-In-Zn-O Thin Film Transistors: A Cation Combinatorial Approach. Journal of the Electrochemical Society, 2011, 158, H433.	2.9	22
113	Enhanced photocurrent of Ge-doped InGaO thin film transistors with quantum dots. Applied Physics Letters, 2015, 106, .	3.3	22
114	Dynamic Logic Circuits Using a-IGZO TFTs. IEEE Transactions on Electron Devices, 2017, 64, 4123-4130.	3.0	22
115	Thin-film transistor behaviour and the associated physical origin of water-annealed Inâ€“Gaâ€“Zn oxide semiconductor. Journal Physics D: Applied Physics, 2012, 45, 415307.	2.8	21
116	Three-dimensionally stacked Al2O3/graphene oxide for gas barrier applications. Carbon, 2017, 125, 464-471.	10.3	21
117	The resonant interaction between anions or vacancies in ZnON semiconductors and their effects on thin film device properties. Scientific Reports, 2017, 7, 2111.	3.3	21
118	Facile fabrication of p-type Al2O3/carbon nanocomposite films using molecular layer deposition. Applied Surface Science, 2018, 458, 864-871.	6.1	21
119	Growth mechanism and diffusion barrier property of plasma-enhanced atomic layer deposition Tiâ€“Siâ€“N thin films. Journal of Vacuum Science & Technology B, 2006, 24, 1327.	1.3	20
120	The Impact of Passivation Layers on the Negative Bias Temperature Illumination Instability of Ha-In-Zn-O TFT. Journal of the Electrochemical Society, 2011, 158, H115.	2.9	20
121	The effect of Ta doping in polycrystalline TiOx and the associated thin film transistor properties. Applied Physics Letters, 2013, 103, .	3.3	20
122	Long-term air-stable Au doping of graphene by layer-by-layer assembly with graphene oxide for flexible transparent electrodes. Carbon, 2018, 126, 241-246.	10.3	20
123	Improved performance and stability of In-Sn-Zn-O thin film transistor by introducing a meso-crystalline ZrO2 high-k gate insulator. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2019, 37, .	2.1	20
124	Impact of tandem IGZO/ZnON TFT with energy-band aligned structure. Applied Physics Letters, 2020, 117, 143505.	3.3	20
125	Low Subthreshold Swing and High Performance of Ultrathin PEALD InGaZnO Thin-Film Transistors. IEEE Transactions on Electron Devices, 2021, 68, 1670-1675.	3.0	20
126	Visible-light phototransistors based on InGaZnO and silver nanoparticles. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2015, 33, .	1.2	19

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127	Atomic layer deposition of indium oxide thin film from a liquid indium complex containing 1-dimethylamino-2-methyl-2-propoxy ligands. Applied Surface Science, 2016, 383, 1-8.	6.1	19
128	The impact of plasma-enhanced atomic layer deposited ZrSiOx insulators on low voltage operated In-Sn-Zn-O thin film transistors. Ceramics International, 2019, 45, 19166-19172.	4.8	19
129	Tailoring nanostructured NbCoSn-based thermoelectric materials via crystallization of an amorphous precursor. Nano Energy, 2021, 80, 105518.	16.0	19
130	Semiconducting properties of amorphous GaZnSnO thin film based on combinatorial electronic structures. Applied Physics Letters, 2014, 104, 182106.	3.3	18
131	Supreme performance of zinc oxynitride thin film transistors via systematic control of the photo-thermal activation process. Journal of Materials Chemistry C, 2018, 6, 5171-5175.	5.5	18
132	Ultra-High-Speed Intense Pulsed-Light Irradiation Technique for High-Performance Zinc Oxynitride Thin-Film Transistors. ACS Applied Materials & Interfaces, 2019, 11, 4152-4158.	8.0	18
133	Transparent Flexible High Mobility TFTs Based on ZnON Semiconductor With Dual Gate Structure. IEEE Electron Device Letters, 2020, 41, 401-404.	3.9	18
134	Significance of Pairing In/Ga Precursor Structures on PEALD InGaO_x Thin-Film Transistor. ACS Applied Materials & Interfaces, 2021, 13, 28493-28502.	8.0	18
135	A High-Reliability Carry-Free Gate Driver for Flexible Displays Using a-IGZO TFTs. IEEE Transactions on Electron Devices, 2018, 65, 3269-3276.	3.0	18
136	Improvement of Morphological Stability of PEALD-Iridium Thin Films by Adopting Two-Step Annealing Process. Electrochemical and Solid-State Letters, 2008, 11, H303.	2.2	17
137	Characteristics and Cleaning of Dry-Etching-Damaged Layer of Amorphous Oxide Thin-Film Transistor. Electrochemical and Solid-State Letters, 2009, 12, H95.	2.2	17
138	Effect of in situ hydrogen plasma treatment on zinc oxide grown using low temperature atomic layer deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2013, 31, 01A124.	2.1	17
139	Enhancement of In-Sn-Ga-O TFT performance by the synergistic combination of UVÂ+ÂO3 radiation and low temperature annealing. Journal of Electroceramics, 2016, 37, 158-162.	2.0	17
140	A morphology, porosity and surface conductive layer optimized MnCo₂O₄ microsphere for compatible superior Li⁺ ion/air rechargeable battery electrode materials. Dalton Transactions, 2016, 45, 5064-5070.	3.3	17
141	Soft Recovery Process of Mechanically Degraded Flexible a-IGZO TFTs With Various Rolling Stresses and Defect Simulation Using TCAD Simulation. IEEE Transactions on Electron Devices, 2020, 67, 535-541.	3.0	17
142	Area-Selective Atomic Layer Deposition of Ruthenium Using a Novel Ru Precursor and H₂O as a Reactant. Chemistry of Materials, 2021, 33, 4353-4361.	6.7	17
143	Mechanical Durability of Flexible/Stretchable a-IGZO TFTs on PI Island for Wearable Electronic Application. ACS Applied Electronic Materials, 2021, 3, 5037-5047.	4.3	17
144	Constant Bias Stress Effects on Threshold Voltage of Pentacene Thin-Film Transistors Employing Polyvinylphenol Gate Dielectric. IEEE Electron Device Letters, 2007, 28, 874-876.	3.9	16

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145	The annealing effect on properties of ZnO thin film transistors with Ti/Pt source-drain contact. Journal of Electroceramics, 2010, 25, 145-149.	2.0	16
146	Molecular orbital ordering in titania and the associated semiconducting behavior. Applied Physics Letters, 2011, 99, 142104.	3.3	16
147	Semiconducting behavior of niobium-doped titanium oxide in the amorphous state. Applied Physics Letters, 2012, 100, .	3.3	16
148	Studies on optical, chemical, and electrical properties of rapid SiO2 atomic layer deposition using tris(tert-butoxy)silanol and trimethyl-aluminum. Materials Research Bulletin, 2012, 47, 3004-3007.	5.2	16
149	Low-cost and flexible ultra-thin silicon solar cell implemented with energy-down-shift via Cd_{0.5}Zn_{0.5}S/ZnS core/shell quantum dots. Journal of Materials Chemistry A, 2015, 3, 481-487.	10.3	16
150	Growth of tantalum nitride film as a Cu diffusion barrier by plasma-enhanced atomic layer deposition from bis((2-(dimethylamino)ethyl)(methyl)amido)methyl(tert-butylimido)tantalum complex. Applied Surface Science, 2016, 362, 176-181.	6.1	16
151	Near-Infrared Photoresponsivity of ZnON Thin-Film Transistor with Energy Band-Tunable Semiconductor. ACS Applied Materials & Interfaces, 2018, 10, 30541-30547.	8.0	16
152	Molecular layer deposition of indicone and organic-inorganic hybrid thin films as flexible transparent conductor. Applied Surface Science, 2020, 525, 146383.	6.1	16
153	Remarkable Stability Improvement with a Highâ€Performance PEALDâ€IZO/IGZO Topâ€Gate Thinâ€Film Transistor via Modulating Dualâ€Channel Effects. Advanced Materials Interfaces, 2022, 9, .	3.7	16
154	Role of the crystallinity of ZnO films in the electrical properties of bottom-gate thin film transistors. Thin Solid Films, 2011, 519, 6801-6805.	1.8	15
155	The growth behavior and properties of atomic layer deposited zinc oxide films using hydrogen peroxide (H2O2) and ozone (O3) oxidants. Ceramics International, 2015, 41, 1839-1845.	4.8	15
156	Organic/Inorganic Hybrid Buffer in InGaZnO Transistors under Repetitive Bending Stress for High Electrical and Mechanical Stability. ACS Applied Materials & Interfaces, 2020, 12, 3784-3791.	8.0	15
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